

Substitute Form PTO-1449 (Modified)  <b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12967-002001	Application No. 09/824,965
	Applicant Tomohiro Kawase et al		
	Filing Date April 3, 2001	Group Art Unit 1765	

**U.S. Patent Documents**

Examiner Initial	Desig. ID	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
<i>AK</i>	AA	5,342,475	8/1994	Yoshida et al.	117/83		
	AB	5,454,346	10/1995	Uchida et al.	117/13		
	AC						
	AD						
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	AJ						
	AK						

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**Foreign Patent Documents or Published Foreign Patent Applications**

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
<i>AK</i>	AL	0 417 843 A2	Mar. 20, 1991	EPO				
	AM	0529963B1	Aug. 21, 1992	EPO				
	AN	04-104989	Apr. 7, 1992	Japan			Abs	
	AO	06-128096	May 10, 1994	Japan			Abs	
	AP							

**Other Documents (include Author, Title, Date, and Place of Publication)**

Examiner Initial	Desig. ID	Document
<i>AK</i>	AQ	Parsey, "Relative virtues of different growth techniques" in Semi-Insulating III-V Materials. 1988.
	AR	Doering et al, "Carbon incorporation into LEC GaAs" in Semi-Insulating III-V Materials. 1990.
	AS	Müller et al, "Current issues in bulk growth of s.i. III-V materials" in Semi-Insulating III-V Materials. 1992.
	AT	Doering et al., "Carbon Incorporation Into LEC GaAs. Int. Conf. Semi-conducting and Semi-Insulating GaAs." Malmö, Sweden (1984)
	AU	Desnica et al., "Distribution coefficient of carbon in gallium arsenide," Inst. Phys. Conf. Ser. No. 83, ch. 2, pp. 33-38 (1986)

Examiner Signature

Date Considered

*3/4/02*

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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f	AV	Desnica et al., "Distribution coefficient of carbon in melt-grown GaAs," J. Appl. Phys. 62(9) (1 Nov. 1987)
f	AW	Kawase et al., "Low-dislocation-density and Low residual-strain Semi-insulating GaAs Grown by VB Method," 9 <sup>th</sup> Conf. on Semiconducting & Insulating Mat'ls-Abstracts, title, contents and p. 47 (April 29-May 3, 1996)
f	AX	Kawase et al., "Low-dislocation-density and Low-residual-strain Semi-insulating GaAs Grown by Vertical Boat Method," 9 <sup>th</sup> Conf. on Semiconducting & Insulating Mat'ls-Proceedings, title, pp. ii-iii, vii-viii, xv, 275-278 (1996)

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